

60V N-Channel Enhancement Mode MOSFET

Voltage 60 V Current 38 A

Features

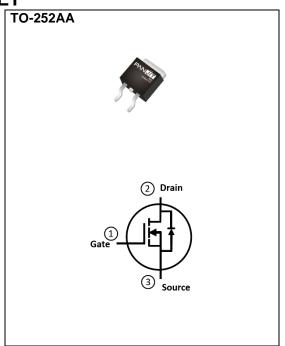
- RDS(ON), VGS@10V, ID@20A<13.5m Ω
- RDS(ON), VGS@4.5V, ID@10A<24m Ω
- Excellent FOM
- Logic Level Drive
- AEC-Q101 qualified
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

Mechanical Data

• Case: TO-252AA Package

• Terminals : Solderable per MIL-STD-750, Method 2026

• Approx. Weight: 0.3217 grams



Maximum Ratings and Thermal Characteristics (T_A=25°C unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNITS	
Drain-Source Voltage		V_{DS}	60	V	
Gate-Source Voltage		V _{GS}	±20	V	
Continuous Drain Current(Note 3)	T _C =25°C		38		
	T _C =100°C	l _D	27	Α	
Pulsed Drain Current(Note 1)	Tc=25°C	I _{DM}	136		
Power Dissipation	Tc=25°C	D-	45	W	
	T _C =100°C	Po	23		
Continuous Drain Current(Note 4)	T _A =25°C	I _D	10.5	А	
	T _A =70°C		9		
Power Dissipation	T _A =25°C	Po	3	W	
	T _A =70°C		2.1		
Single Pulse Avalanche Current ^(Note 5)		I _{AS}	22	Α	
Single Pulse Avalanche Energy ^(Note 5)		Eas	41	mJ	
Operating Junction and Storage Temperature Range		T _J ,T _{STG}	-55~175	°C	
Thermal Resistance ^(Note 4)	Junction to Case	R _{θJC}	3.8	°C/W	
	Junction to Ambient	R _{θJA}	50		



Electrical Characteristics (T_A=25°C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS	
Static							
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =250uA 60 -		-	-	.,	
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250uA	1.5	2.1	3	V	
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} =10V, I _D =20A	1	10.6	13.5	mΩ	
		V _{GS} =4.5V, I _D =10A	-	18.8	24		
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =60V, V _{GS} =0V	1	-	1	uA	
Gate-Source Leakage Current	I _{GSS}	V _{GS} =±20V, V _{DS} =0V	ı	-	±100	nA	
Dynamic ^(Note 6)							
Total Gate Charge	Qg		ı	16	21	nC	
Gate-Source Charge	Qgs	V _{DS} =30V, I _D =20A,	ı	3	-		
Gate-Drain Charge	Q_{gd}	V _{GS} =10V	-	4	-		
Input Capacitance	Ciss	\/ 00\/ \/ 0\/	ı	800	1120	pF	
Output Capacitance	Coss	V _{DS} =30V, V _{GS} =0V,	ı	273	410		
Reverse Transfer Capacitance	Crss	f=1MHz	ı	28	-		
Gate resistance	Rg	f=1MHz	ı	1.3	-	Ω	
Turn-On Delay Time	td _(on)		-	6.5	-		
Turn-On Rise Time	t _r	V _{DS} =30V, I _D =20A,	-	19	-	ns	
Turn-Off Delay Time	td _(off)	$V_{GS}=10V, R_{G}=3\Omega$	ı	15	-		
Turn-Off Fall Time	tf	(11010 2)	ı	15	-		
Drain-Source Diode							
Diode Forward Current	Is	T _C =25°C	-	-	38	А	
Pulsed Diode Forward Current	I _{SM}	Tc=25 C	-	-	136		
Diode Forward Voltage	V _{SD}	I _S =20A, V _{GS} =0V		0.85	1.3	V	
Reverse Recovery Time	Trr	V _{DD} =30V,V _{GS} =0V	-	16	-	ns	
Reverse Recovery Charge	Qrr	I _S =20A,dI _S /dt=100A/us	-	5	-	nC	

NOTES:

- 1. Pulse width<a>100us, Duty cycle<a>2%.
- 2. Essentially independent of operating temperature typical characteristics.
- 3. Chip capability with an R_{0JC}=3.8°C/W.
- 4. R_{BJA} is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch² with 2oz.square pad of copper.
- 5. Eas is calculated based on the condition of L=1mH, I_{AS}=9A, V_{DD}=30V, V_{GS}=10V. 100% test at L=0.1mH, I_{AS}=22A in production.
- 6. Guaranteed by design, not subject to production testing.



TYPICAL CHARACTERISTIC CURVES

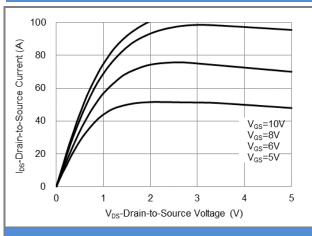


Fig.1 On-Region Characteristics

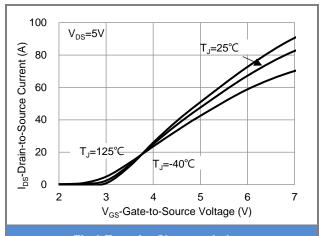


Fig.2 Transfer Characteristics

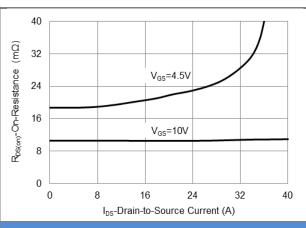


Fig.3 On-Resistance vs. Drain Current

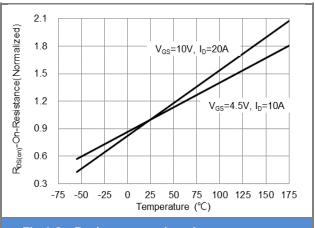
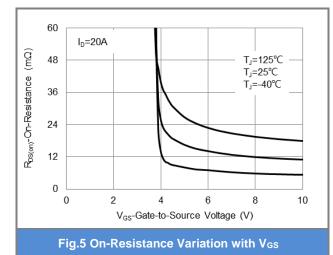


Fig.4 On-Resistance vs. Junction temperature



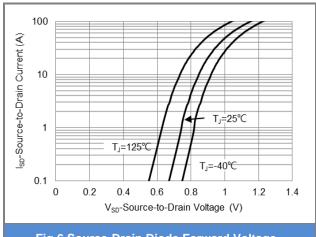


Fig.6 Source-Drain Diode Forward Voltage



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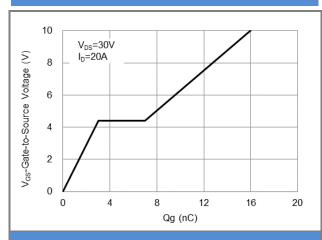


Fig.7 Gate-Charge Characteristics

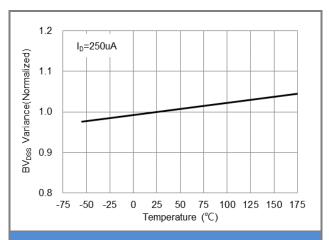


Fig.8 Breakdown Voltage Variation vs. Temperature

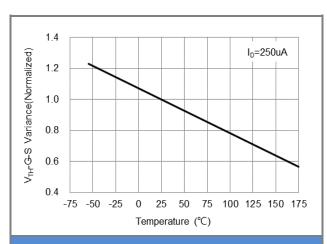


Fig.9 Threshold Voltage Variation with Temperature

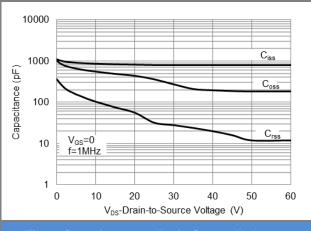
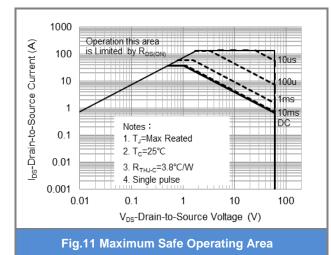


Fig.10 Capacitance vs. Drain-Source Voltage



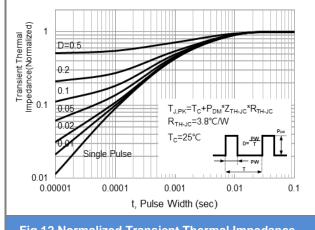


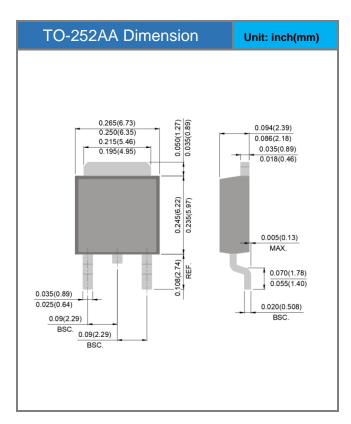
Fig.12 Normalized Transient Thermal Impedance

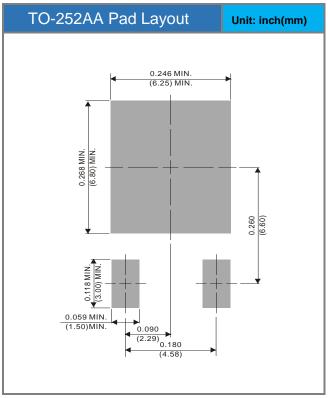


Product and Packing Information

Part No.	Package Type	Packing Type	Marking	
PJD45N06SA-AU	TO-252AA	3K pcs / 13" reel	45N06SA	

Packaging Information & Mounting Pad Layout







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